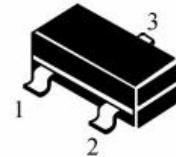


ISS187/ISS190/ISS196

**SOT-23 Switching Diode 开关二极管****■ Internal Configuration& Device Marking 内部结构与产品打标**

Type 型号	ISS187	ISS190	ISS196
Pin 管脚	1 o —> 3 2 o	1 o 2 o —> 3	1 o 2 o —> 3
Mark 打标	D3	E3	G3

■ Absolute Maximum Ratings 最大额定值

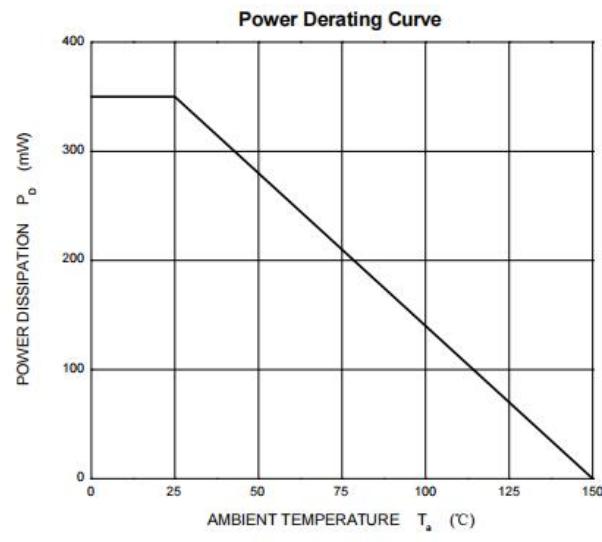
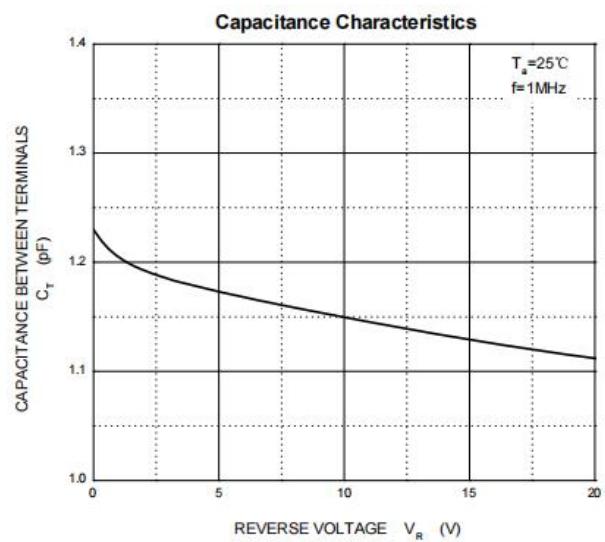
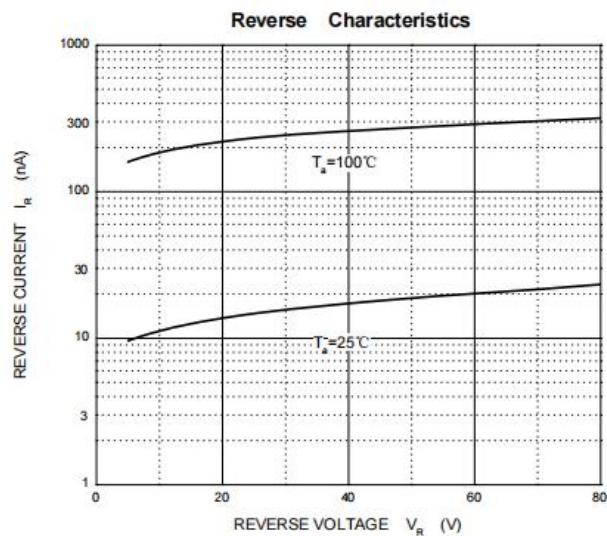
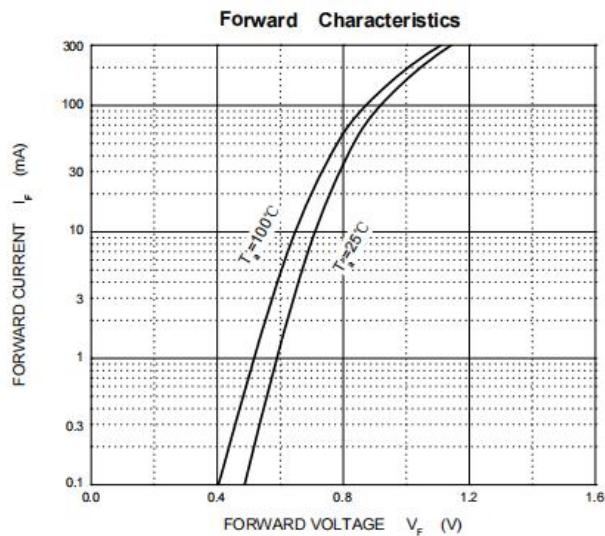
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V _{RRM}	80	V
Reverse Work Voltage 反向工作电压	V _{RWM}		
DC Reverse Voltage 直流反向电压	V _R		
Forward Work Current 正向工作电流	I _F (I _O)	100	mA
Peak Forward Current 正向峰值电流	I _{FM}	300	mA
Power dissipation 耗散功率	P _D (Ta=25°C)	150	mW
Thermal Resistance J-A 结到环境热阻	R _{θJA}	833	°C/W
Junction and Storage Temperature 结温和储藏温度	T _J , T _{stg}	-55 to +150°C	

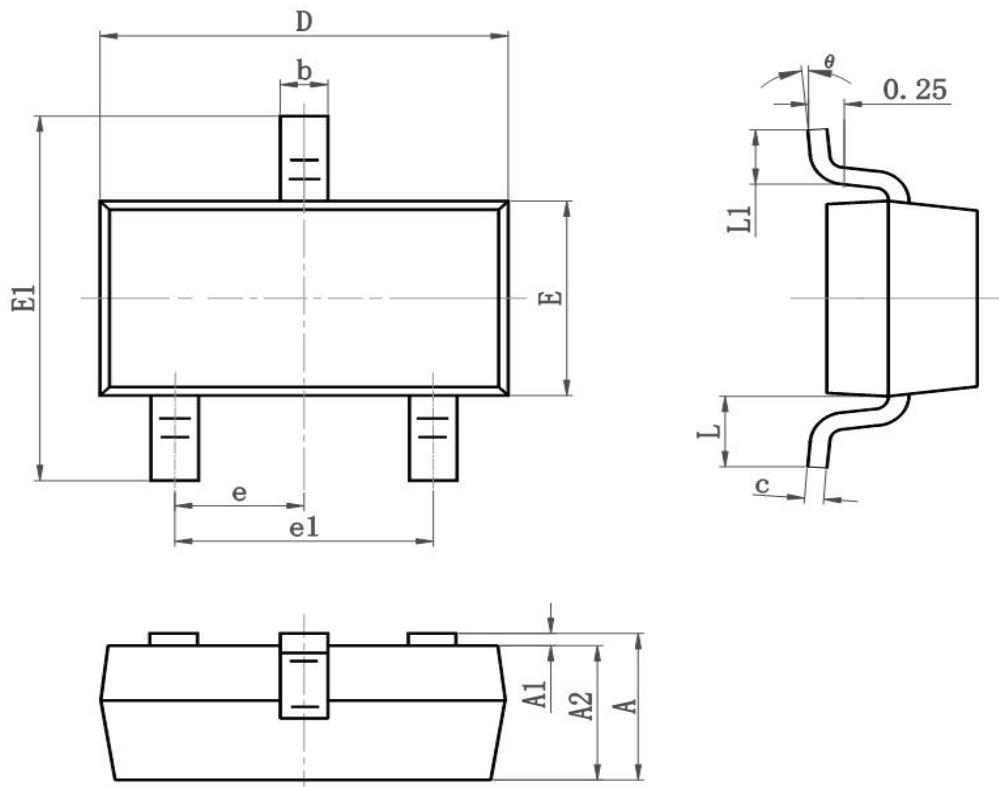
■ Electrical Characteristics 电特性

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压(I _R =100μA)	V _(BR)	80	—	—	V
Reverse Leakage Current(VR=30V) 反向漏电流(VR=80V)	I _R	—	—	0.1 0.5	μA
Forward Voltage(I _F =1mA) 正向电压(I _F =10mA) (I _F =100mA)	V _F	—	0.61 0.74 0.92	1.2	V
Diode Capacitance 二极管电容(V _R =0V, f=1MHz)	C _D	—	—	3	pF
Reverse Recovery Time 反向恢复时间	T _{rr}	—	—	4	nS

■Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.900	1.00	0.035	0.039
e1	1.800	2.000	0.071	0.079
L	0.500	0.600	0.020	0.024
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°